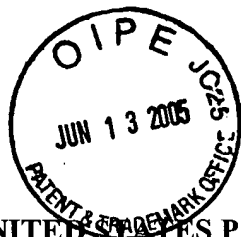


Docket No.: 2336-255



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Inventor(s): Seung Wan CHAE

U.S. Patent Application No. 10/812,015

Filed: March 30, 2004

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: Confirmation No. 2799
:
: Group Art Unit: 2811
:
: Examiner: Hung K. Vu

For: GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE
AND METHOD FOR MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

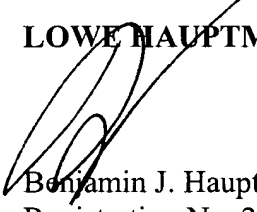
Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Respectfully submitted,

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